

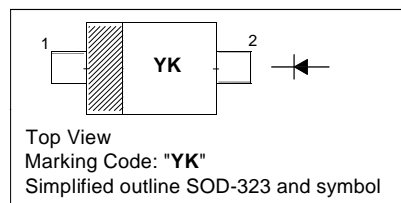
## SCHOTTKY BARRIER DIODE

### Features

- Low power rectified
- Silicon epitaxial type
- High reliability

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	30	V
Forward Current	$I_F$	0.2	A
Repetitive Peak Forward Current	$I_{FRM}$	0.5	A
Non-Repetitive Peak Forward Current (8.3 ms)	$I_{FSM}$	1	A
Power Dissipation	$P_D$	150	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$ at $I_F = 30\text{ mA}$	$V_F$	0.4 0.5	V
Reverse Current at $V_R = 30\text{ V}$	$I_R$	1	$\mu\text{A}$
Total Capacitance at $V_R = 1\text{ V}$ , $f = 1\text{ MHz}$	$C_T$	10	$\text{pF}$



Fig. 1  $I_F - V_F$

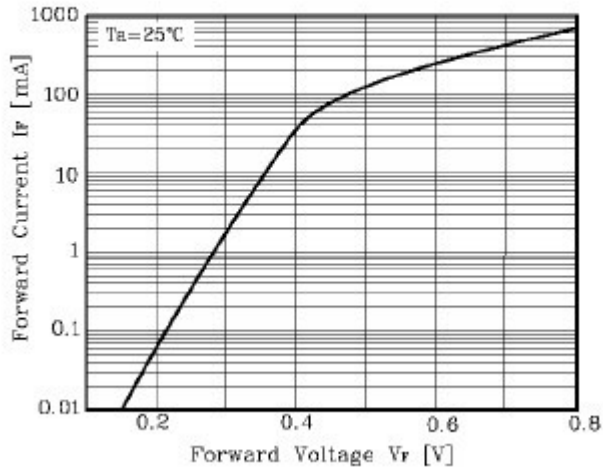


Fig. 2  $I_R - V_R$

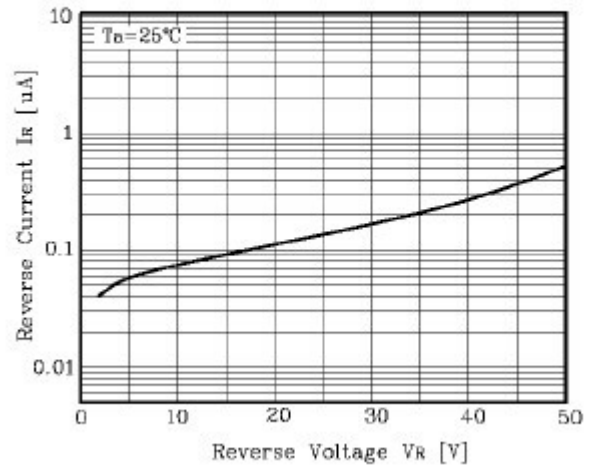
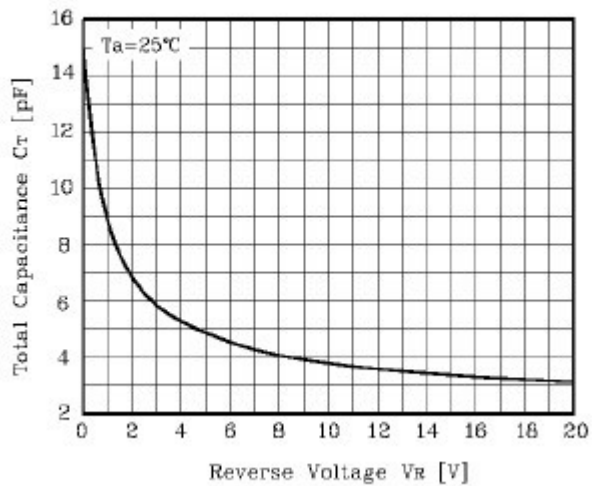


Fig. 3  $C_T - V_R$





**CHINA BASE**  
INTERNATIONAL

**SOD-323**



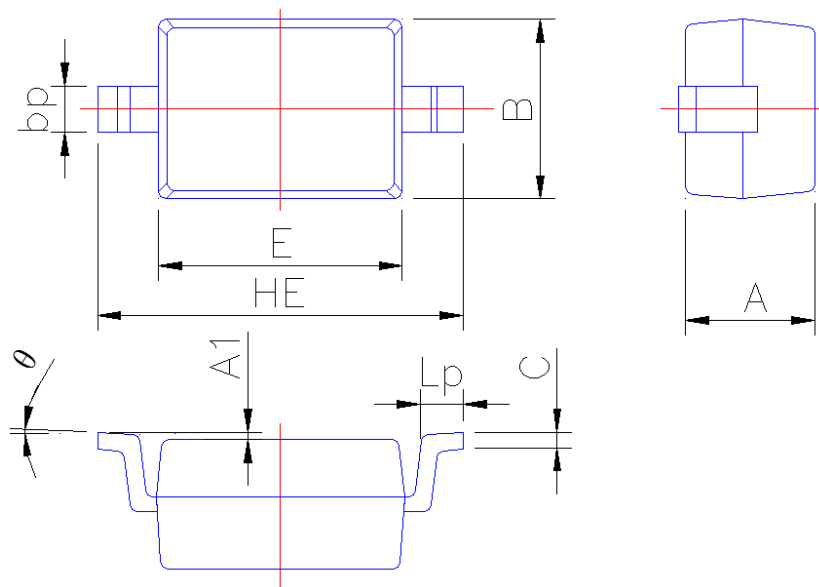
**SDB310WS**

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**PACKAGE OUTLINE**

Plastic surface mounted package; 2 leads

SOD-323



Symbol	Dimension in Millimeters	
	Min	Max
A	0.95	1.15
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.40
C	0.09	0.150
E	1.60	1.80
HE	2.30	2.70
Lp	0.20	0.40
θ	0°	5°